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NXP Semiconductors/Freescale Semiconductor, Inc. BT138-600,127

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BT138-600

4Q Triac 29 August 2013

Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	95	A
Tj	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 99 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	12	A
Static chara	acteristics	· · · · ·				
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	5	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	8	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	10	35	mA







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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	22	70	mA
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package	ackage				
	Name	Description	Version			
BT138-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT138-600/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 99 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	95	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	105	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	45	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

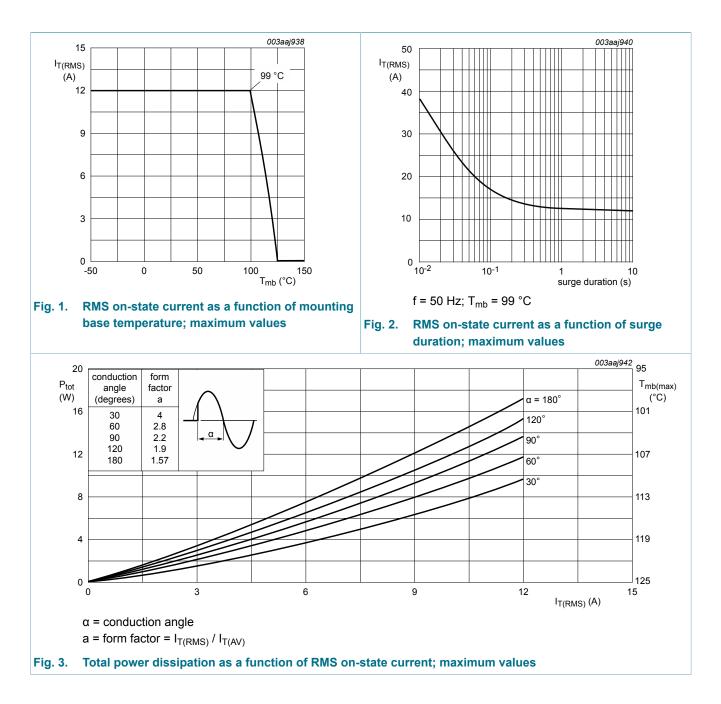


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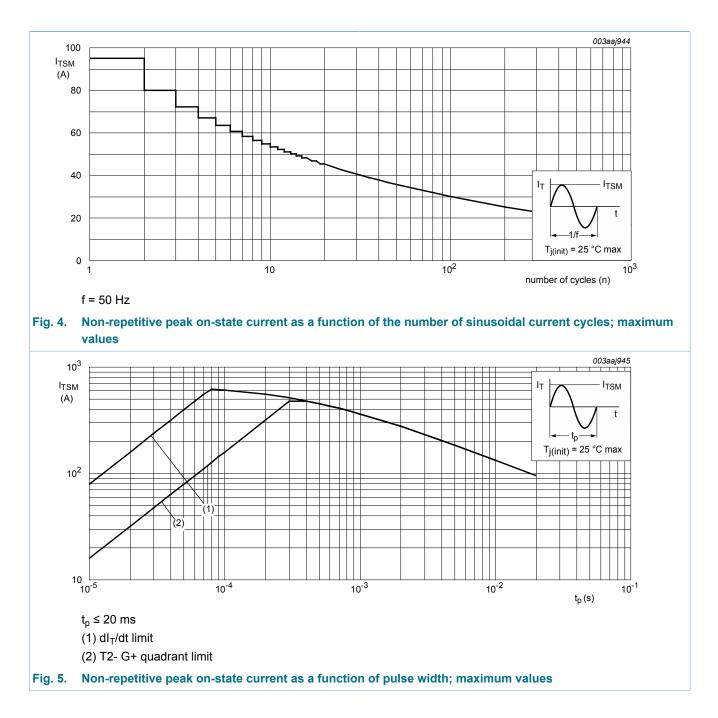
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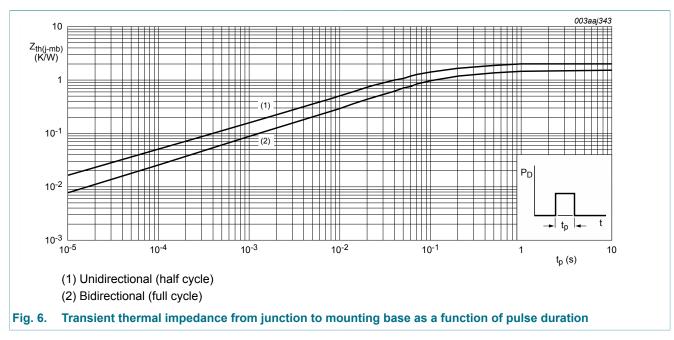


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Thermal characteristics 8.

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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9. Characteristics

$ \begin{split} & \prod_{j=25\ cC;\ Fig.\ T} & & & & & & & & & & $	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Static chara	acteristics	· · · · · ·				
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	I _{GT}	gate trigger current		-	5	35	mA
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$				-	8	35	mA
$ \begin{array}{ c c c c c c } \hline T_{j} = 25 \ ^{\circ}\text{C}; \ \overline{Fig}, \overline{7} & & & & & & & & & & & & & & & & & & &$				-	10	35	mA
$ \begin{array}{ c c c c c c c } \hline T_{j} = 25 \ ^{\circ}C; \ \overline{Fig. 8} & & & & & & & & & & & & & & & & & & $				-	22	70	mA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	IL I	latching current		-	7	40	mA
$ \frac{T_{j} = 25 \ ^{\circ}C; \ Fig. 8}{V_{D} = 12 \ V; \ I_{G} = 0.1 \ A; \ T_{2} - G+; \ T_{j} = 25 \ ^{\circ}C; \ Fig. 9}{P_{1} = 25 \ ^{\circ}C; \ Fig. 9} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $				-	20	60	mA
$ \begin{array}{ c c c c c c c } \hline T_{j} = 25 \ ^{\circ}\text{C}; \ \ \ \ Fig. 8 & & & & & & & & & & & & & & & & & & $				-	8	40	mA
$V_{T} \qquad \text{on-state voltage} \qquad I_{T} = 15 \text{ A}; T_{j} = 25 ^{\circ}\text{C}; Fig. 10 \qquad - \qquad 1.4 \qquad 1.65$ $V_{GT} \qquad gate trigger voltage \qquad V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}; T_{j} = 25 ^{\circ}\text{C}; \qquad - \qquad 0.7 \qquad 1 \qquad V_{D} = 400 \text{ V}; I_{T} = 0.1 \text{ A}; T_{j} = 125 ^{\circ}\text{C}; \qquad 0.25 \qquad 0.4 \qquad - \qquad Fig. 11 \qquad V_{D} = 400 \text{ V}; I_{T} = 0.1 \text{ A}; T_{j} = 125 ^{\circ}\text{C}; \qquad 0.25 \qquad 0.4 \qquad - \qquad Fig. 11 \qquad V_{D} = 600 \text{ V}; T_{j} = 125 ^{\circ}\text{C}; \qquad - \qquad 0.1 \qquad 0.5$ $Dynamic characteristics \qquad V_{D} = 600 \text{ V}; T_{j} = 125 ^{\circ}\text{C}; (V_{DM} = 67\% \qquad - \qquad 0.1 \qquad 0.5 \qquad - \qquad 0.1 \qquad 0.5$				-	10	60	mA
$ V_{GT} = \begin{cases} gate trigger voltage \\ V_{D} = 12 V; I_{T} = 0.1 A; T_{j} = 25 °C; \\ Fig. 11 \\ V_{D} = 400 V; I_{T} = 0.1 A; T_{j} = 125 °C; \\ Fig. 11 \\ V_{D} = 400 V; I_{T} = 0.1 A; T_{j} = 125 °C; \\ Fig. 11 \\ V_{D} = 600 V; T_{j} = 125 °C \\ V_{D} = 10 V; T_{j} = 125 °C \\ V_{D} = 10 V; T_{j} = 125 °C \\ V_{D} = 10 V; T_{j} = 125 °C \\ V_{D} = 10 V; T_{j} $	I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	6	30	mA
$\frac{Fig. 11}{V_{D} = 400 \text{ V}; I_{T} = 0.1 \text{ A}; T_{j} = 125 ^{\circ}\text{C};} & 0.25 & 0.4 & -\frac{1000 \text{ C}}{Fig. 11} & 0.5 & 0.4 & -\frac{1000 \text{ C}}{Fig.$	VT	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
Fig. 11Image: Second systemFig. 11Image: Second systemImage: Second system <td>V_{GT}</td> <td>gate trigger voltage</td> <td>,</td> <td>-</td> <td>0.7</td> <td>1</td> <td>V</td>	V _{GT}	gate trigger voltage	,	-	0.7	1	V
Dynamic characteristics dV_D/dt rate of rise of off-state voltage $V_{DM} = 402 \text{ V}; \text{ T}_j = 125 ^{\circ}\text{C}; (V_{DM} = 67\%)of V_{DRM}); exponential waveform; gateopen circuit100250-$,	0.25	0.4	-	V
$\frac{dV_D}{dt} \qquad rate of rise of off-state voltage \qquad V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67\% of V_{DRM}); exponential waveform; gate open circuit \qquad 100 250 -$	I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
voltage of V _{DRM}); exponential waveform; gate open circuit	Dynamic ch	naracteristics	· · · · ·	1		1	
tet gate-controlled turn-on $I_{TM} = 16 \text{ A}$; $V_D = 600 \text{ V}$; $I_C = 0.1 \text{ A}$; $dI_C/$ - 2 -	dV _D /dt		of V_{DRM}); exponential waveform; gate	100	250	-	V/µs
time $dt = 5 A/\mu s$	t _{gt}	gate-controlled turn-on time	I_{TM} = 16 A; V _D = 600 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

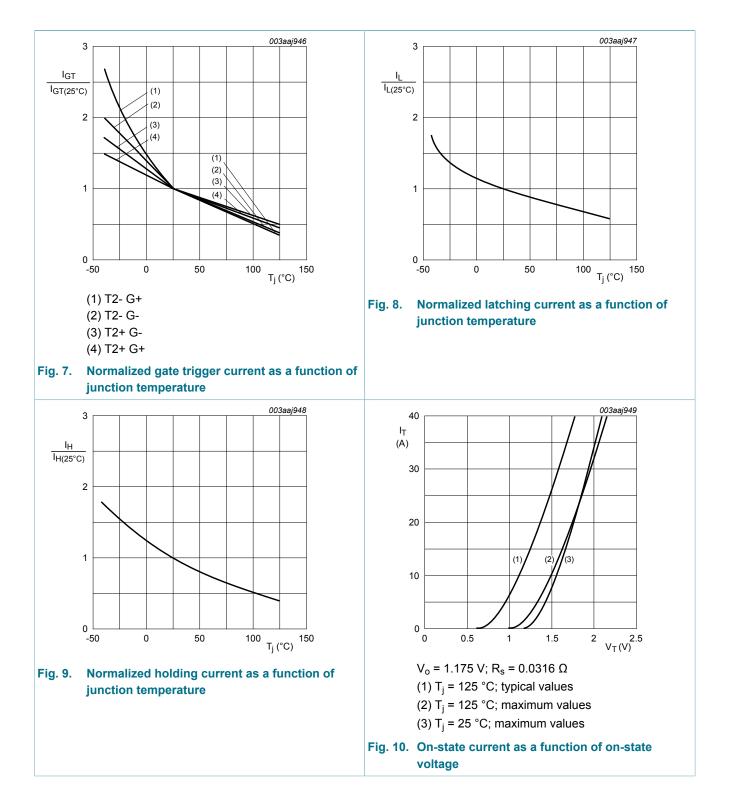


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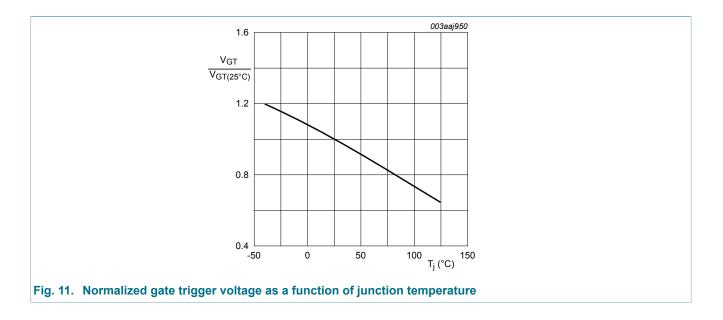
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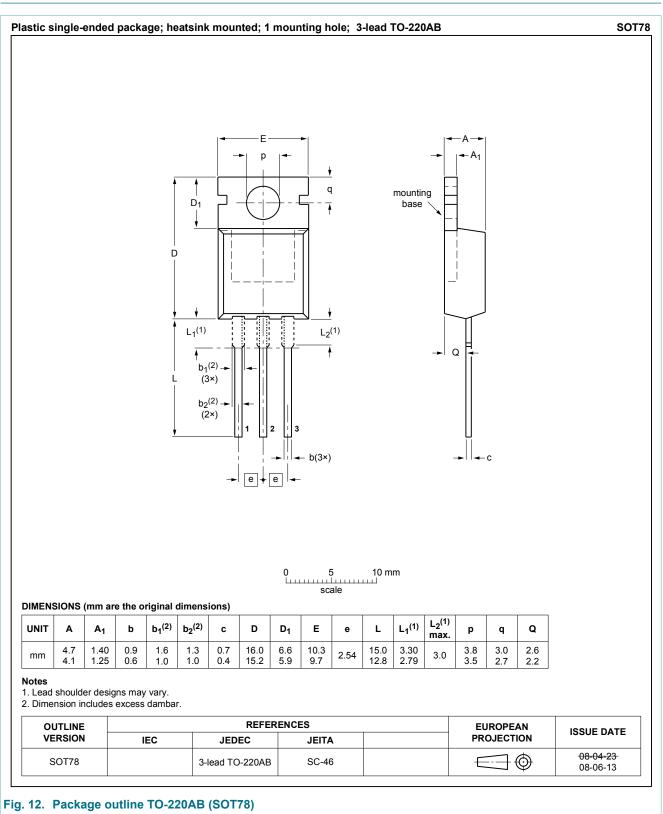
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10. Package outline



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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